

Silicon NPN Power Transistors

2SC3762

DESCRIPTION

- With TO-3PML package
- High speed switching
- High current capability

APPLICATIONS

- For use in high speed and power switching applications

PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | Base |
| 2 | Collector |
| 3 | Emitter |

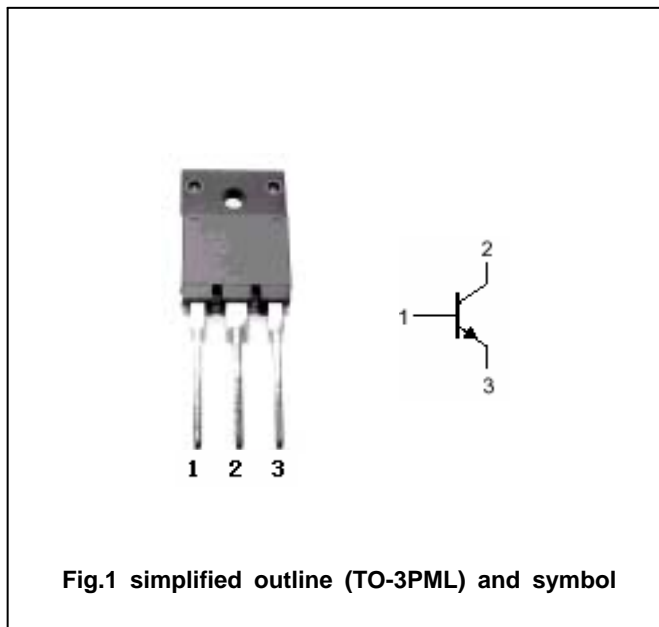


Fig.1 simplified outline (TO-3PML) and symbol

Absolute maximum ratings (Ta=25)

| SYMBOL | PARAMETER | CONDITIONS | MAX | UNIT |
|------------------|---------------------------|--------------------|---------|------|
| V _{CBO} | Collector-base voltage | Open emitter | 150 | V |
| V _{CEO} | Collector-emitter voltage | Open base | 100 | V |
| V _{EBO} | Emitter-base voltage | Open collector | 6 | V |
| I _C | Collector current | | 15 | A |
| P _C | Collector dissipation | T _C =25 | 65 | W |
| T _j | Junction temperature | | 150 | |
| T _{stg} | Storage temperature | | -55~150 | |

Silicon NPN Power Transistors

2SC3762

CHARACTERISTICS

T_j=25 unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|----------------------|--------------------------------------|---|-----|------|-----|------|
| V _{(BR)CEO} | Collector-emitter breakdown voltage | I _C =25mA ; I _B =0 | 100 | | | V |
| V _{(BR)CBO} | Collector-base breakdown voltage | I _C =1mA ; I _E =0 | 150 | | | V |
| V _{(BR)EBO} | Emitter-base breakdown voltage | I _E =1mA ; I _C =0 | 6 | | | V |
| V _{CEsat} | Collector-emitter saturation voltage | I _C =10A ; I _B =1A | | | 0.6 | V |
| V _{BEsat} | Base-emitter saturation voltage | I _C =10A ; I _B =1A | | | 1.5 | V |
| I _{CBO} | Collector cut-off current | V _{CB} =100V ; I _E =0 | | | 10 | μ A |
| I _{EBO} | Emitter cut-off current | V _{EB} =4V ; I _C =0 | | | 10 | μ A |
| h _{FE} | DC current gain | I _C =5A ; V _{CE} =5V | 30 | | 120 | |

Silicon NPN Power Transistors

2SC3762

PACKAGE OUTLINE

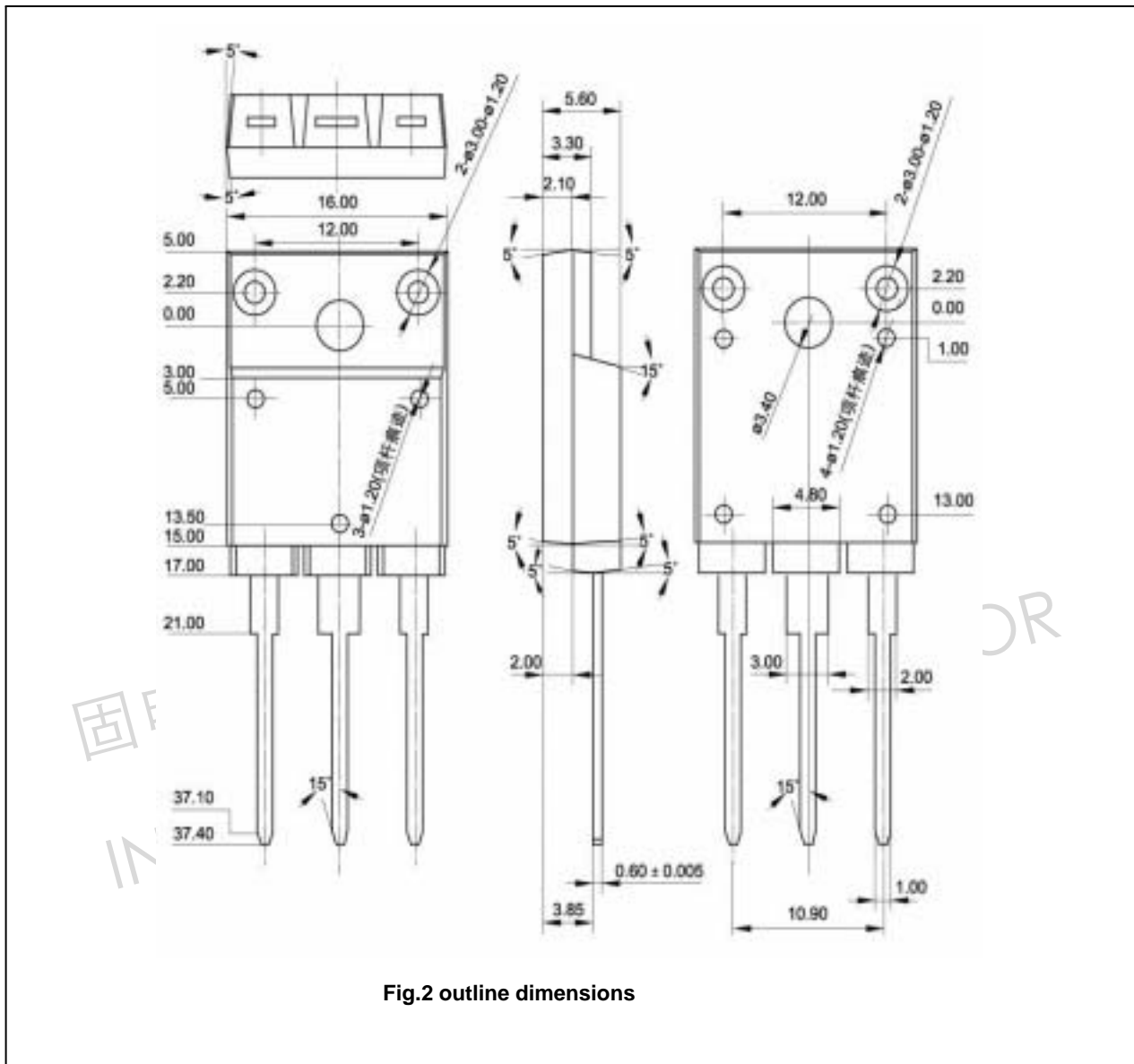


Fig.2 outline dimensions